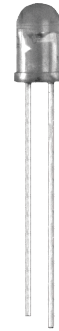


NPN Silicon Phototransistor

OP599 Series



Features:

- Dark blue injection-molded plastic package
- Variety of sensitivity ranges
- T-1 $\frac{3}{4}$ package style with TO-18 base
- Excellent optical lens surface
- Excellent chip placement

Description:

Each device in this series consists of a NPN silicon phototransistor mounted in a dark blue plastic injection molded shell package, with a narrow receiving angle that provides excellent on-axis coupling and optical/mechanical axis alignment. The shell also provides excellent optical lens surface, control of chip placement and consistency of the outside package dimensions.

The **OP599** series sensors are 100% production tested for close correlation with OPTEK GaAlAs emitters.

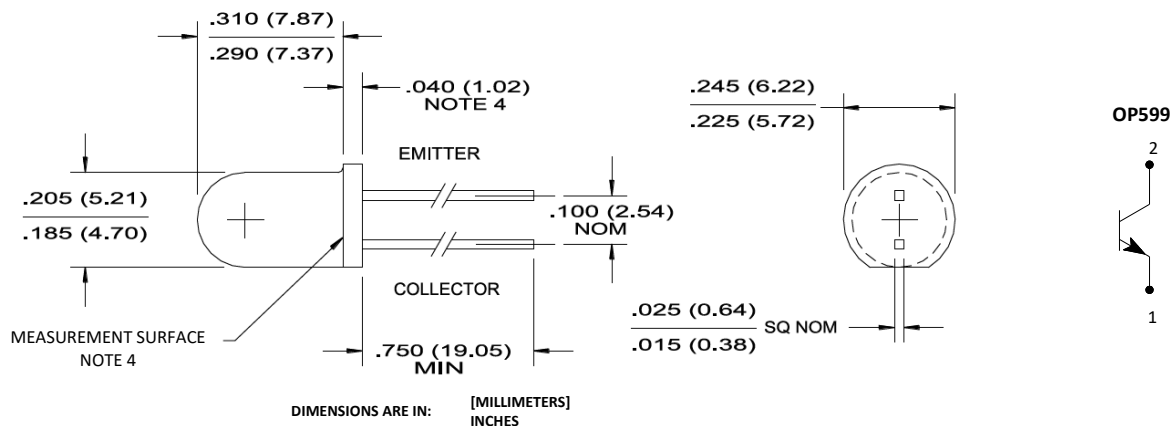
Please refer to Application Bulletin 210 for additional thermal design information.

Applications:

- Applications requiring a narrow receiving angle
- Applications that are space-limited

Ordering Information

Part Number	Sensor	Viewing Angle	Lead Length
OP599A	Transistor	20°	0.75"
OP599C			



RoHS

Pin #	Sensor
1	Emitter
2	Collector

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To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK's molded plastics.

General Note

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NPN Silicon Phototransistor

OP599 Series



Electrical Specifications

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage and Operating Temperature Range	-40° C to +100° C
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Continuous Collector Current	50 mA
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron] ⁽¹⁾	260° C
Power Dissipation ⁽²⁾	100 mW

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$I_{C(ON)}$ ⁽³⁾	On-State Collector Current OP599A OP599C	2.35 0.40	- -	- 1.95	mA	$V_{CE} = 5\text{ V}$, $E_E = 0.25\text{ mW/cm}^2$
I_{CEO}	Collector-Dark Current	-	-	100	nA	$V_{CE} = 10.0\text{ V}$, $E_E = 0$
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30	-	-	V	$I_C = 100\text{ }\mu\text{A}$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0	-	-	V	$I_E = 100\text{ }\mu\text{A}$
$V_{CE(SAT)}$ ⁽³⁾	Collector-Emitter Saturation Voltage	-	-	0.40	V	$I_C = 100\text{ }\mu\text{A}$, $E_E = 0.25\text{ mW/cm}^2$

Notes:

1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum 20 grams force may be applied to the leads when soldering.
2. Derate linearly 1.07 mW/°C above 25° C.
3. Light source is an unfiltered GaAlAs emitting diode operating at peak emission wavelength of 890 nm.
4. This dimension is held to within $\pm 0.005''$ on the flange edge and may vary up to $\pm 0.020''$ in the area of the leads.

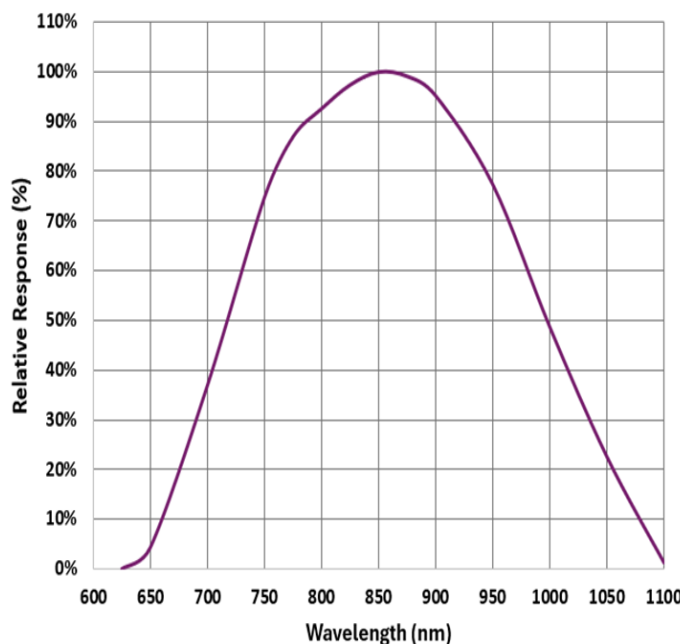
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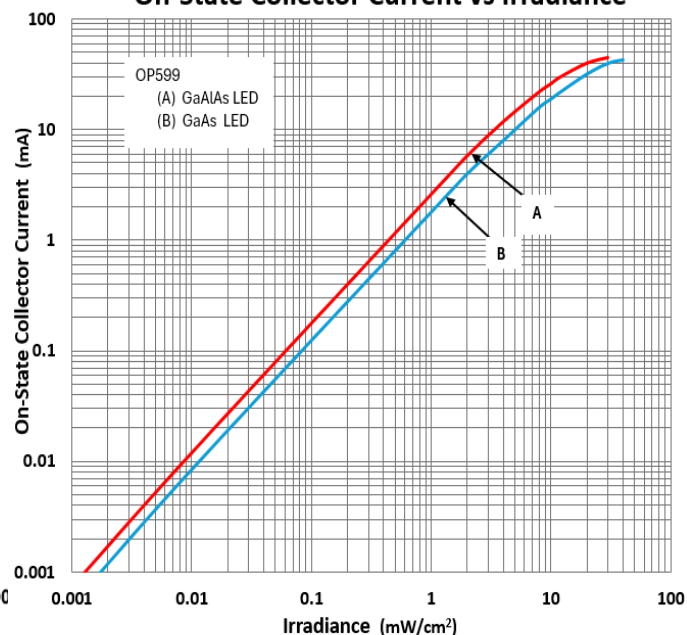
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Typical Performance

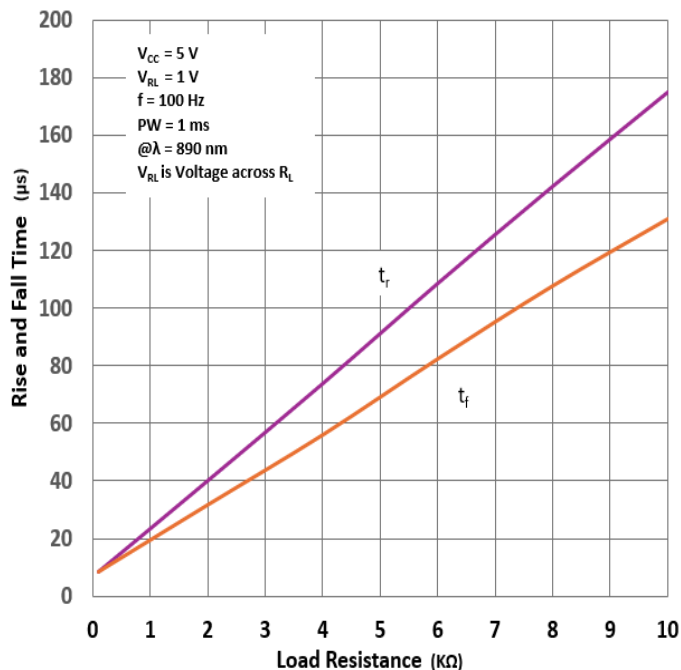
Typical Spectral Response



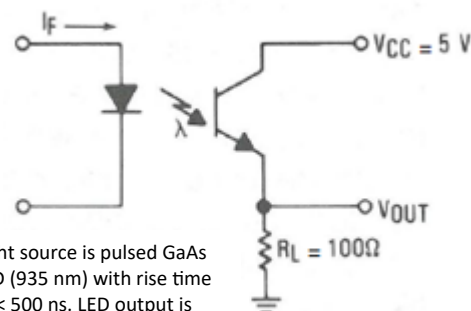
On-State Collector Current vs Irradiance



Rise and Fall Times vs Load Resistance



Test Circuit



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